

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

MSOP07CDR

产品手册

概述

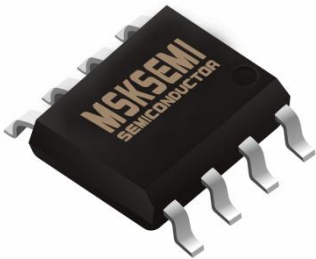
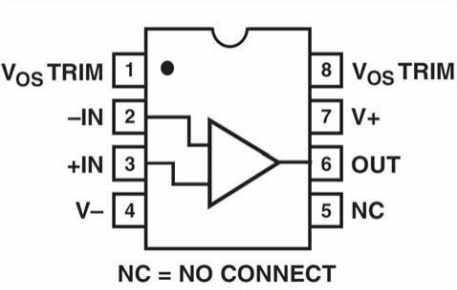

MSOP07CDR 是一个高精密运算放大器，其最大失调电压控制在 150uV。增益达 200V/mV。因MSOP07CD特别适用于仪表等方面。

MSOP07CDR 有着较宽的输入电压范围($\pm 13V$)，以及高达 100dB 以上的共模抑制比 (CMRR)，其在高闭环增益电路中亦保持出色的线性度和增益精度。

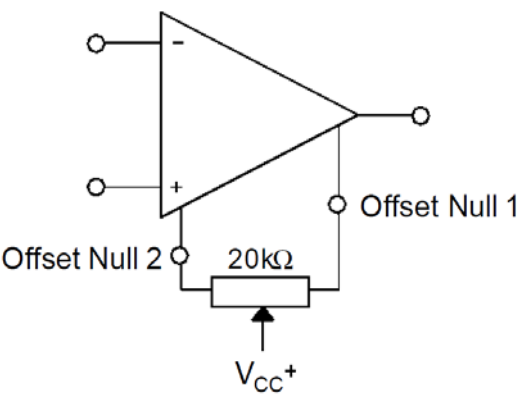
主要特点

- 最大失调电压. 150uV MAX
- 低失调电流 $I_{io}=1.3nA$ typ
- 工作电压范围宽 $\pm 3V$ to $\pm 20V$

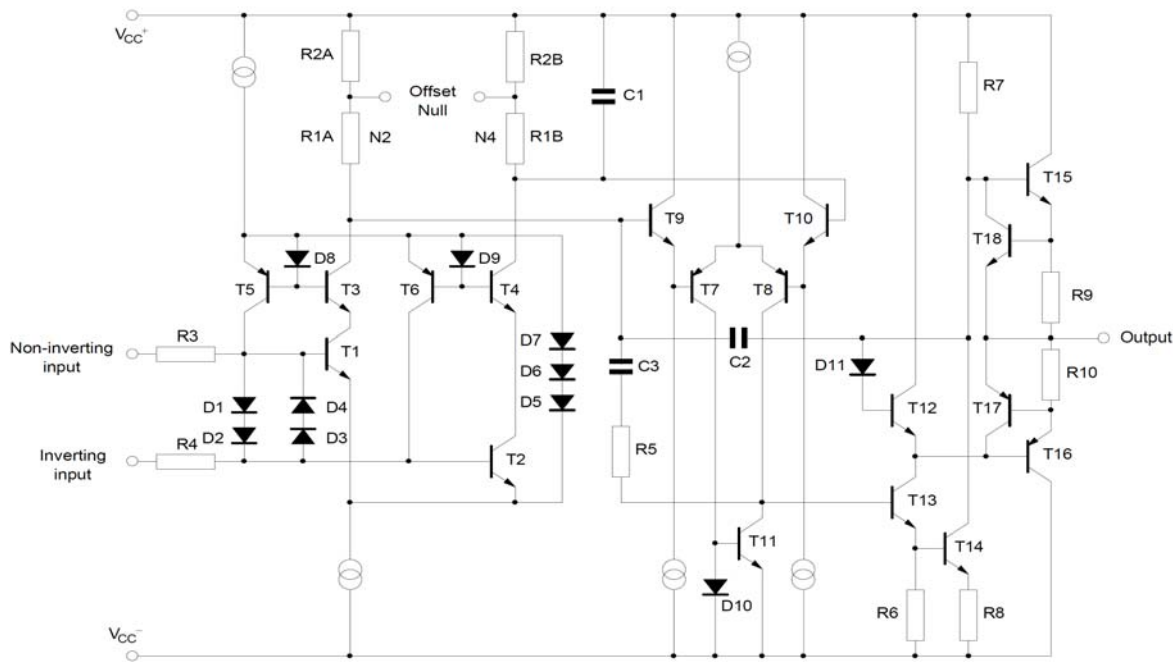
引脚描述和标记

SOP-8	引脚说明	管体标记
		<div></div> <p>**= Internal production code</p>

输入失调调零电路



框图



极限参数（绝对最大额定值，若无其它规定，Tamb=25℃）

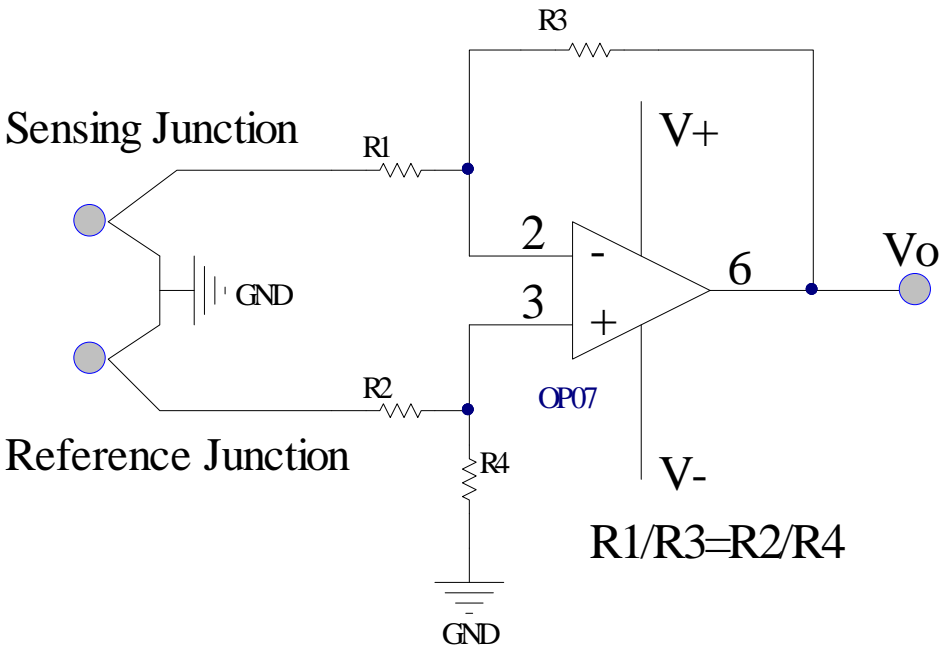
参数名称	符号	数值	单位
电源电压	Vcc	±20	V
输入电压	Vi	±18	V
输入差动电压	Vid	±30	V
工作温度	TOPR	-10~+85	℃
贮存温度	TSTG	-40~+150	℃

电特性（Vcc=±15V，Tamp=25℃ 特殊情况另外说明）

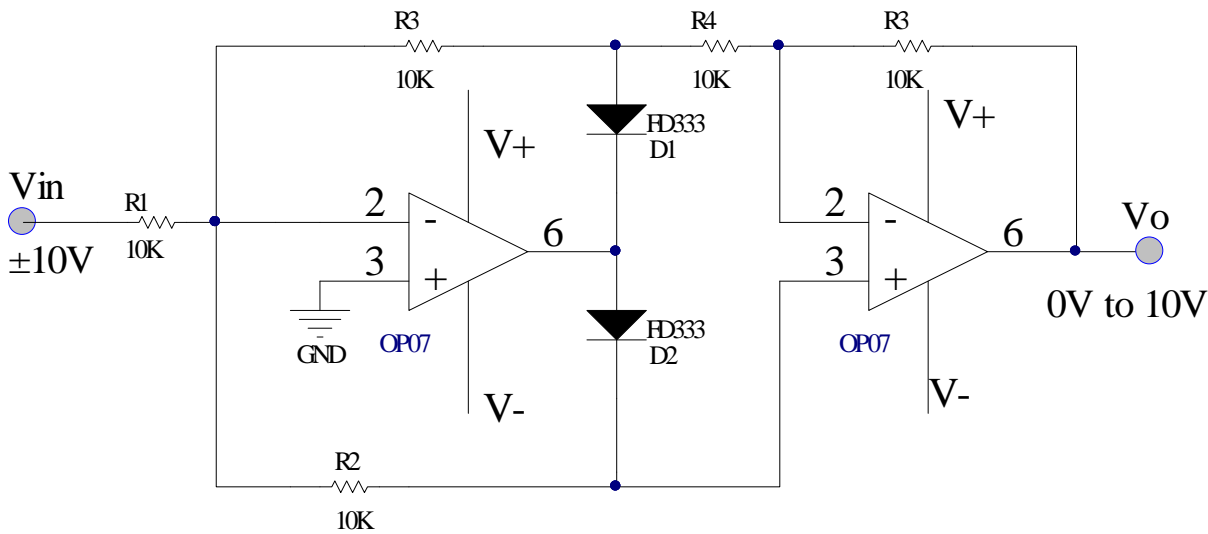
符 号	描 述	数 值			单 位
		最小值	典型值	最大值	
Vio	失调电压 0℃<Tamb<70℃			150	uV
				250	uV
DVio	失调温度漂移			1.8	uV/℃
Iio	输入失调电流			8	nA
Iib	输入偏置电流			28	nA
Vicm	输入共模电压 0℃<Tamb<70℃	±13 ±13	±13.5		V
CMR	共模抑制比	100			dB
SVR	电源抑制比	90			dB
Avd	Large Signal Voltage Gain VCC =±15V, RL= 2kΩ, VO=±10V,	100			V/mV

V _{opp}	输出峰值 R _L = 10k Ω R _L = 2k Ω	±12 ±11.5			V
GBP	增益带宽 R _L = 2k Ω, C _L = 100pF, f = 100KHz)		0.5		MHz
ICC	电源电流 (no load) 0℃ <T _{amb} <70℃ V _{CC} = ±3V		3.8 1	6 3	mA

典型应用图

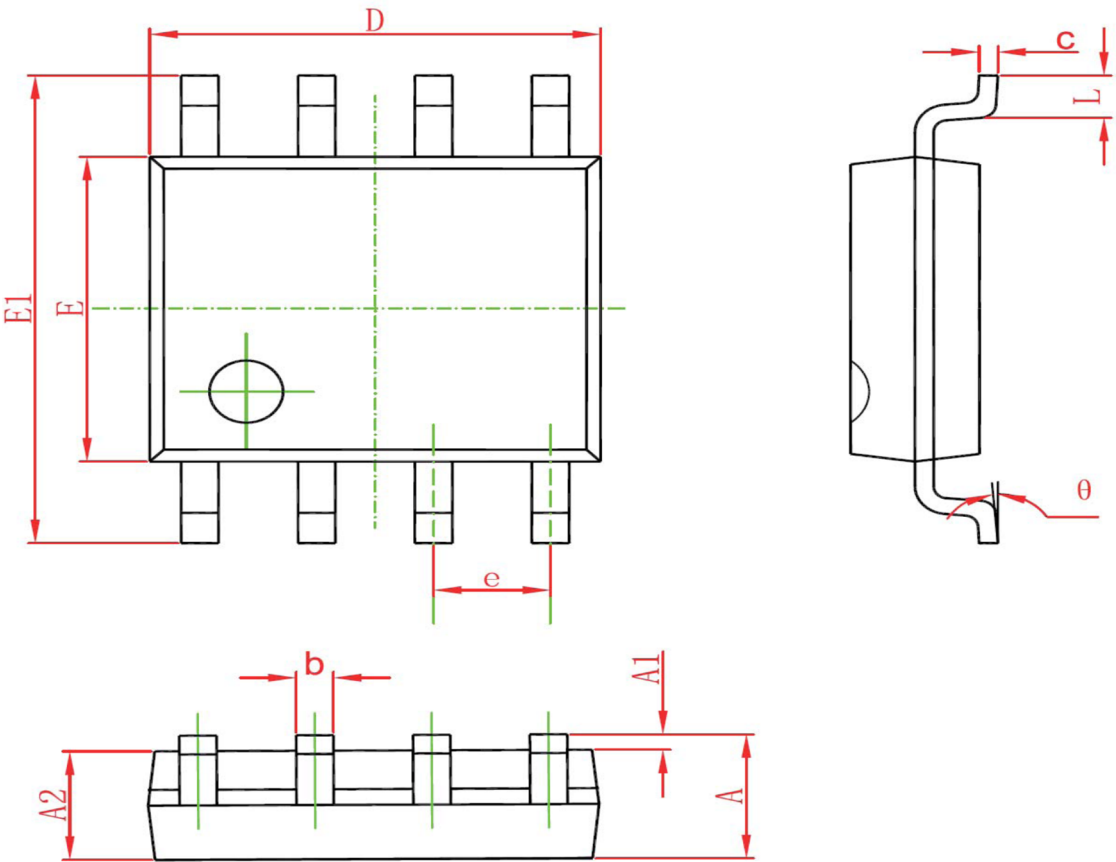


高稳定热电偶放大



精密绝对值电路

封装图（SOP-8）



符号	毫米（mm）		英寸（Inch）	
	最小值	最大值	最小值	最大值
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	1.550	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.27(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050

订货信息

料号	封装	包装
MSOP07CDR	SOP8	2500PCS

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